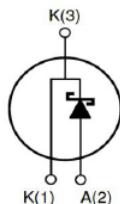




TO-220AC(S)



TO-220AC



Internal Schematic

**Features**

- Rated to 1200V at 5 Amps
- Zero reverse recovery current
- Zero forward recovery voltage
- Temperature independent switching behaviour
- High temperature operation
- High frequency operation
- Marking : ESIC05120S

**Benefits**

- Unipolar rectifier
- Substantially reduced switching losses
- No thermal run-away with parallel devices
- Reduced heat sink requirements

**Ordering Information**

Part No.	Package	Packing
ESIC05120S	TO-220AC	
ESIC05120S-S	TO-220AC(S)	50 / Tube

**Application**

- SMPS, e.g., CCM PFC
- Motor drives, Solar application, UPS, Wind turbine, Rail traction, EV/HEV

**Absolute Maximum Ratings ( $T_A=25^\circ\text{C}$  unless otherwise specified)**

Parameter	Symbol	Conditions	Limit	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	$T_j=25^\circ\text{C}$	1200	V
Surge Peak Reverse Voltage	$V_{RSM}$	$T_j=25^\circ\text{C}$	1200	V
DC Blocking Voltage	$V_{DC}$	$T_j=25^\circ\text{C}$	1200	V
Continuous Forward Current	$I_F$	$T_j=25^\circ\text{C}$ $T_j=135^\circ\text{C}$ $T_j=150^\circ\text{C}$	18 8.5 5	A
Repetitive Peak Forward Surge Current	$I_{FRM}$	$T_C=25^\circ\text{C}$ , $tp=10\text{ms}$ , Half Sine Wave, $D=0.3$	25	A
Non-Repetitive Peak Forward Surge Current	$I_{FSM}$	$T_C=25^\circ\text{C}$ , $tp=10\text{ms}$ , Half Sine Wave	35	A
Power Dissipation	$P_{TOT}$	$T_C=25^\circ\text{C}$	109.5	W
		$T_C=110^\circ\text{C}$	47	W
Maximum Case Temperature	$T_C$		135	$^\circ\text{C}$
Operating Junction and Storage Temperature	$T_j \cdot T_{stg}$		-55~+175	$^\circ\text{C}$
Mounting Torque		M3 Screw 6-32 Screw	1 8.8	Nm lbf-in
Thermal resistance from junction to case	$R_{\theta JC}$		1.37 Typ.	$^\circ\text{C}/\text{W}$



ESIC05120S

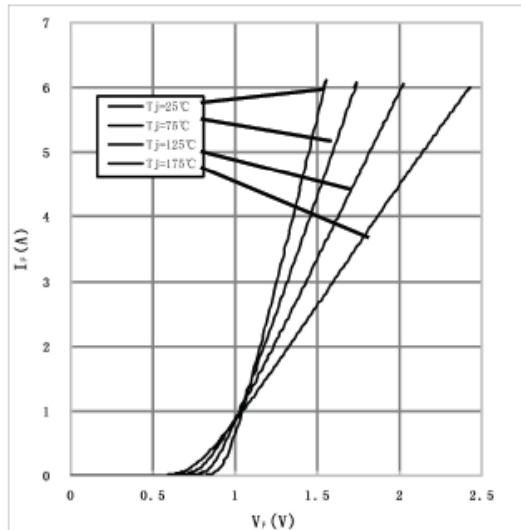
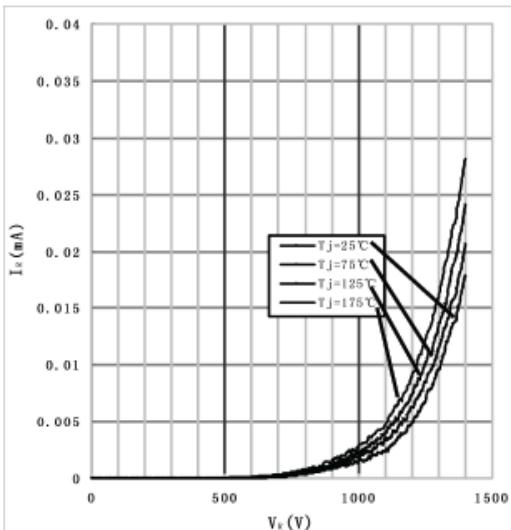
RoHS Pb

## Silicon carbide power schottky diode

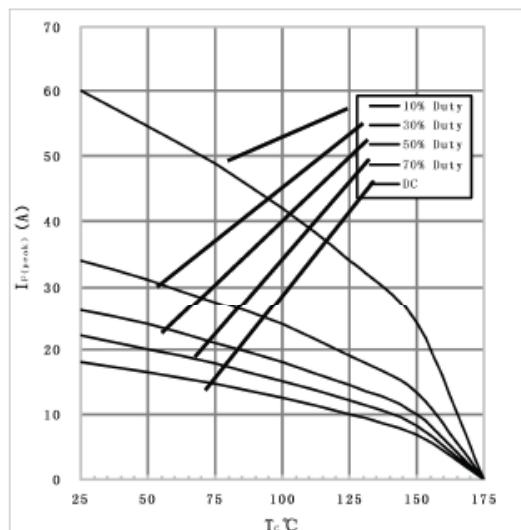
Electrical Characteristics ( $T_A = 25^\circ C$  unless otherwise specified)

Parameter	Conditions	Symbol	Min.	Typ.	Max.	Unit
Forward Voltage	$I_F=5A, T_j=25^\circ C$	$V_F$	-	1.45	1.8	V
	$I_F=5A, T_j=175^\circ C$		-	2.05	2.5	
Reverse Current	$V_R=1200V, T_j=25^\circ C$	$I_R$	-	20	100	$\mu A$
	$V_R=1200V, T_j=175^\circ C$		-	50	200	
Total Capacitive Charge	$V_R=800V, T_j=150^\circ C$ $Q_c = \int_0^{V_R} C(V) dV$	$Q_c$	-	36	-	nC
Total Capacitive Charge	$V_R=0V, T_j=25^\circ C, f=1MHz$	C	-	475	510	pF
	$V_R=400V, T_j=25^\circ C, f=1MHz$		-	34	44	
	$V_R=800V, T_j=25^\circ C, f=1MHz$		-	33	40	

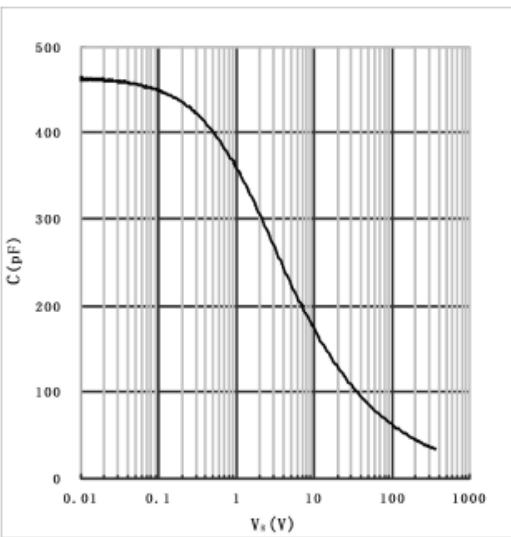
## Rating and Characteristics Curves

1) Forward IV characteristics as a function of  $T_j$ :2) Reverse IV characteristics as a function of  $T_j$ :

3) Current Derating



4) Capacitance vs. reverse voltage :



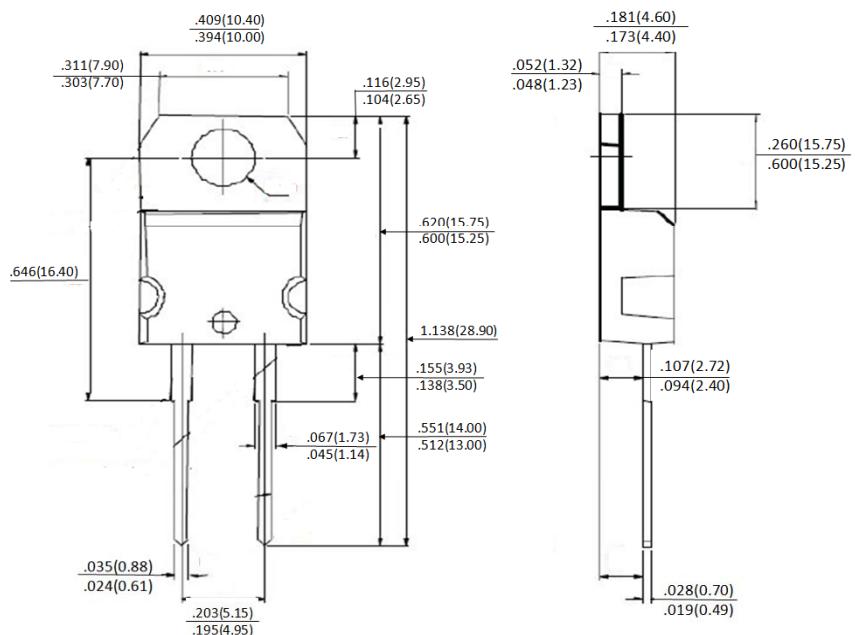


ESIC05120S

RoHS Pb

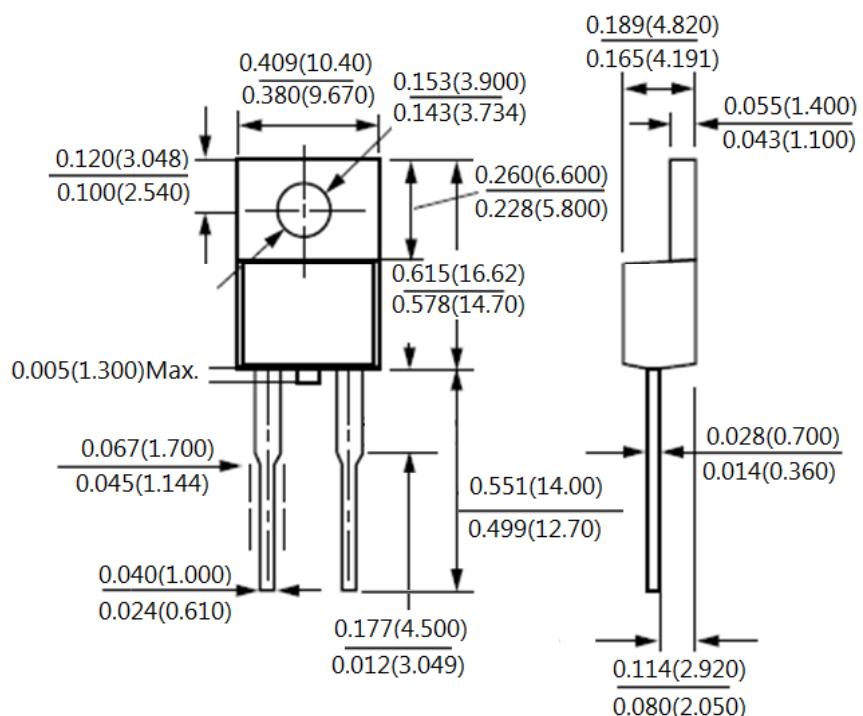
Silicon carbide power schottky diode

**Package Outline Dimensions**



TO-220AC(S)

Dimensions in inches and (millimeters)



TO-220AC

Dimensions in inches and (millimeters)